

# **BB506M**

# Built in Biasing Circuit MOS FET IC UHF RF Amplifier

REJ03G1604-0100 Rev.1.00 Nov 26, 2007

# Features

- Built in Biasing Circuit; To reduce using parts cost & PC board space.
- High gain
- www.DataSheet4U. $\overrightarrow{PG} = 24 \text{ dB}$  typ. (f = 900 MHz)
  - Low noise
  - NF = 1.4 dB typ. (f = 900 MHz)
  - Low output capacitance
    - Coss = 1.1 pF typ. (f = 1 MHz)
  - Provide mini mold packages: CMPAK-4 (SOT-343mod)

### Outline

RENESAS Package code: PLSP0004ZA-A (Package name: MPAK-4)



1. Source 2. Gate1 3. Gate2 4. Drain

Notes: 1. Marking is "FS-".

2. BB506M is individual type number of RENESAS BBFET.

# **Absolute Maximum Ratings**

ltem	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DS</sub>	6	V
Gate1 to source voltage	V <sub>G1S</sub>	+6	V
		-0	
Gate2 to source voltage	V <sub>G2S</sub>	+6	V
		-0	
Drain current	Ι <sub>D</sub>	30	mA
Channel power dissipation	Pch <sup>Note3</sup>	300	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 3. Value on the glass epoxy board (50 mm  $\times$  40 mm  $\times$  1 mm).

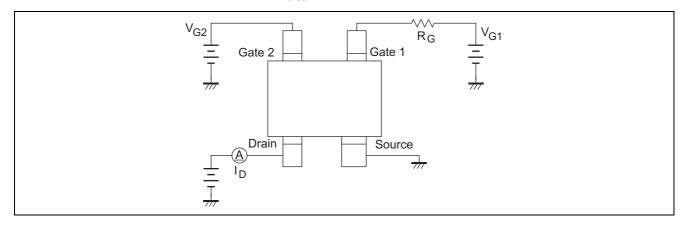
This device is sensitive to electro static discharge. An adequate careful handling procedure is requested.

 $(T_{0} - 25^{\circ}C)$ 

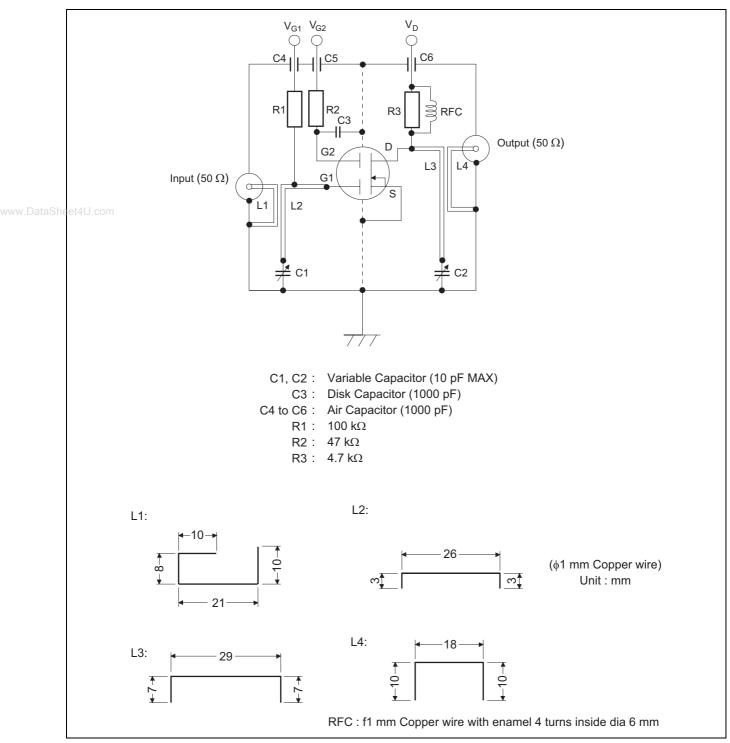
# **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	6	_	—	V	$I_D = 200 \ \mu A, \ V_{G1S} = V_{G2S} = 0$
Gate1 to source breakdown voltage	V <sub>(BR)G1SS</sub>	+6	_	—	V	$I_{G1}$ = +10 µA, $V_{G2S}$ = $V_{DS}$ = 0
Gate2 to source breakdown voltage	V <sub>(BR)G2SS</sub>	+6	—	_	V	$I_{G2}$ = +10 µA, $V_{G1S}$ = $V_{DS}$ = 0
Gate1 to source cutoff current	I <sub>G1SS</sub>	_	_	+100	nA	$V_{G1S} = +5 V, V_{G2S} = V_{DS} = 0$
Gate2 to source cutoff current	I <sub>G2SS</sub>	—	_	+100	nA	$V_{G2S}$ = +5 V, $V_{G1S}$ = $V_{DS}$ = 0
Gate1 to source cutoff voltage	V <sub>G1S(off)</sub>	0.5	0.8	1.1	V	$V_{DS}$ = 5 V, $V_{G2S}$ = 4 V, $I_{D}$ = 100 $\mu$ A
Gate2 to source cutoff voltage	V <sub>G2S(off)</sub>	0.4	0.7	1.0	V	$V_{DS} = 5 \text{ V}, V_{G1S} = 5 \text{ V}, I_D = 100 \ \mu\text{A}$
Drain current	I <sub>D(op)</sub>	12	16	20	mA	
Forward transfer admittance	y <sub>fs</sub>	27	32	38	mS	
Input capacitance	Ciss	1.2	1.6	2.0	pF	$V_{DS} = 5 V, V_{G1} = 5 V, V_{G2S} = 4 V$
Output capacitance	C <sub>oss</sub>	0.7	1.1	1.5	pF	$R_{G} = 100 \text{ k}\Omega, \text{ f} = 1 \text{ MHz}$
Power gain	PG	19	24	29	dB	$V_{DS} = 5 V, V_{G1} = 5V, V_{G2S} = 4 V$
Noise figure	NF	_	1.4	2.1	dB	$R_{G} = 100 \text{ k}\Omega, \text{ f} = 900 \text{ MHz}$

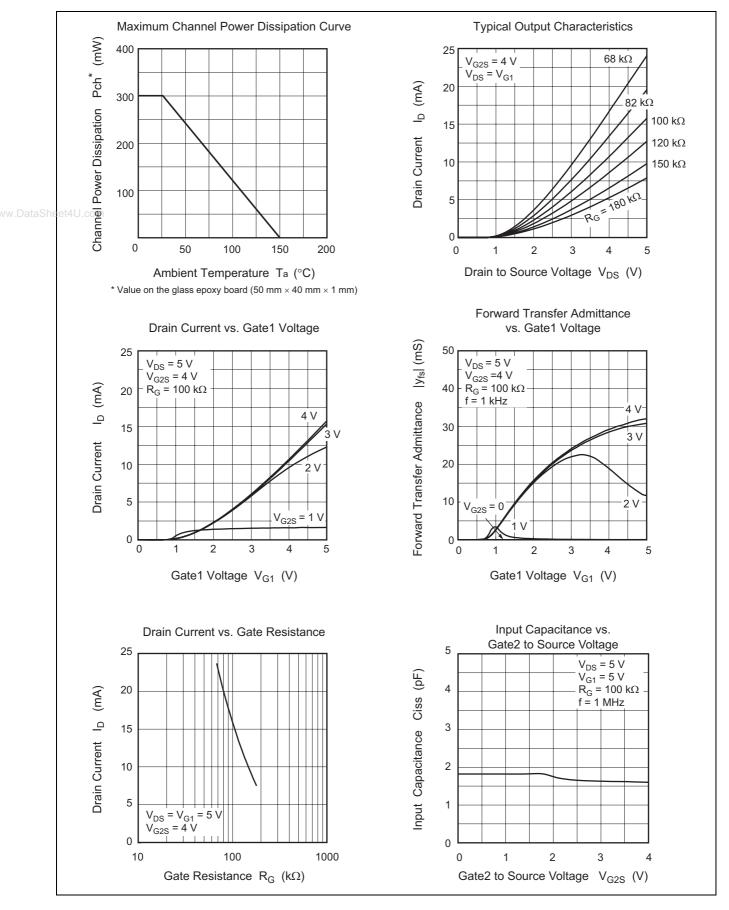
# Bias Circuit for Operating Items ( $I_{D(op)}$ , $|y_{fs}|$ , Ciss, Coss, NF, PG)



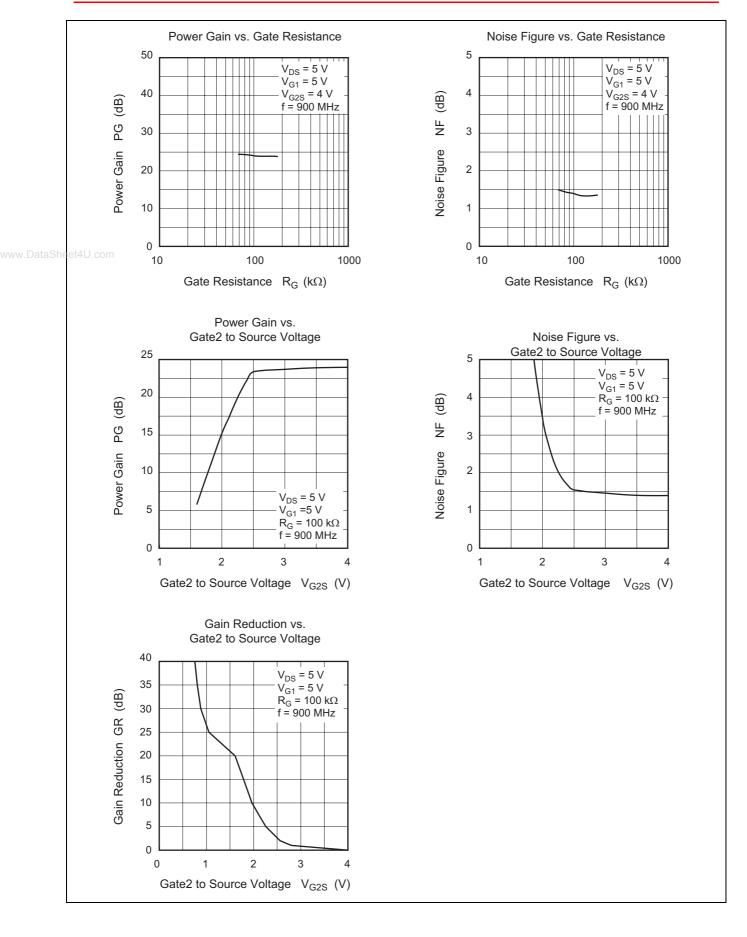


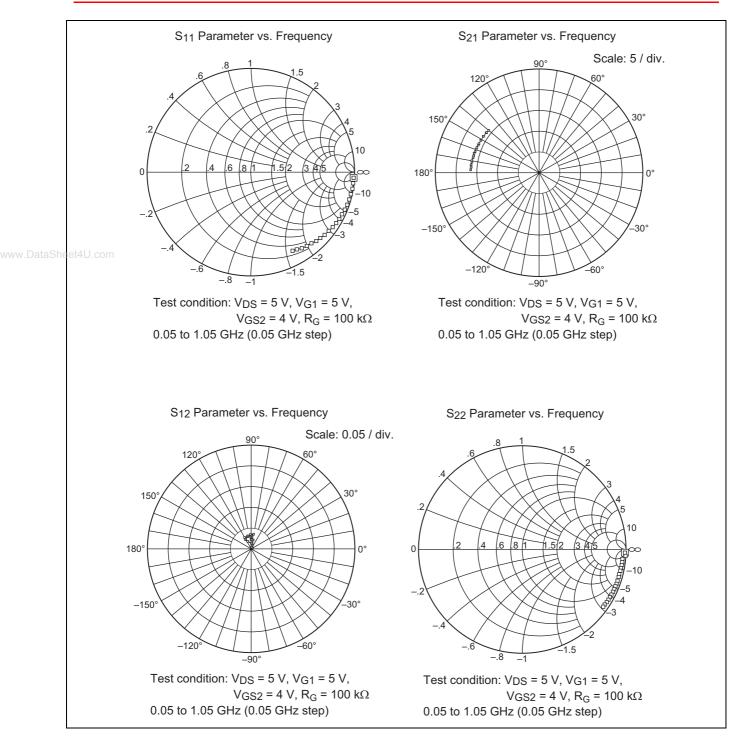


### **Main Characteristics**



RENESAS



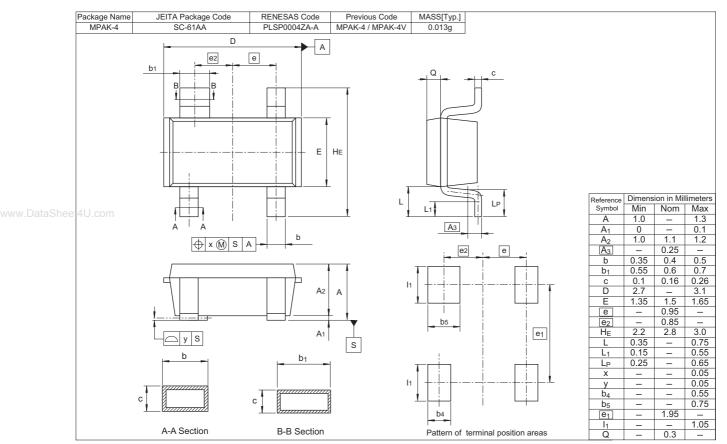


# S parameter

$(V_{DS} = 5 V, V_{G1} = 5 V, V_{G2S})$	$= 4 \text{ V}, \text{ R}_{\text{G}} = 100 \text{ k}\Omega, \text{ Zo} = 50 \Omega$ )
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Freq	req S11 S21		S21	S	12	S22		
(MHz)	Mag	Deg	Mag	Deg	Mag	Deg	Mag	Deg
50	0.995	-3.3	3.28	177.9	0.001	17.6	0.991	-1.8
100	0.991	-6.2	3.26	175.5	0.001	75.6	0.996	-3.6
150	0.992	-9.3	3.28	173.7	0.002	73.8	0.995	-5.2
200	0.987	-12.4	3.26	171.3	0.002	79.5	0.997	-7.0
250	0.984	-15.5	3.27	170.0	0.004	116.5	0.995	-8.6
300	0.981	-18.6	3.24	167.3	0.003	89.6	0.993	-10.3
350	0.975	-21.7	3.23	165.8	0.004	76.3	0.992	-11.8
400	0.967	-24.8	3.24	163.3	0.004	87.0	0.989	-13.9
heet4U.co <b>450</b>	0.964	-27.9	3.22	161.9	0.004	91.9	0.991	-15.5
500	0.958	-30.8	3.22	159.4	0.006	89.0	0.987	-17.0
550	0.951	-33.9	3.22	157.9	0.006	100.4	0.988	-18.9
600	0.939	-37.0	3.20	155.4	0.004	84.2	0.985	-20.4
650	0.933	-40.3	3.20	154.1	0.004	85.4	0.984	-22.2
700	0.922	-43.5	3.20	150.7	0.007	80.4	0.983	-23.7
750	0.916	-46.5	3.19	150.7	0.007	93.5	0.981	-25.5
800	0.900	-49.6	3.19	146.7	0.006	108.8	0.979	-27.2
850	0.892	-52.8	3.18	146.4	0.005	122.9	0.978	-28.9
900	0.883	-56.2	3.18	142.8	0.005	120.3	0.975	-30.6
950	0.866	-59.2	3.17	142.3	0.006	104.0	0.970	-32.3
1000	0.858	-62.0	3.16	139.8	0.006	121.3	0.970	-33.8

# **Package Dimensions**



# **Ordering Information**

Part Name	Quantity	Shipping Container
BB506MFS-TL-E	3000	Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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